

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>	Docket Number (Optional) <b>FIS920030377US1</b>	Application Number <b>10/716,785</b>
	Applicant(s) <b>Huang, et al.</b>	
	Filing Date <b>11/19/2003</b>	Group Art Unit <b>1752</b>

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
S.J.L.		US 5,712,078	01/27/1998	Huang, et al.	430	270.1	
↓		US 5,919,597	07/06/1999	Sinta, et al.	430	270.1	

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

**OTHER DOCUMENTS** *(Including Author, Title, Date, Pertinent Pages, Etc.)*

S.J.L.		Schmaljohann, et al - "Design Strategies for 157 nm Single-Layer Photoresists: Lithographic Evaluation of a Poly (a-trifluoromethyl vinyl alcohol) Copolymer Department of Material Science and Engineering, Cornell University In advances in Resist Technology and Processing XVII, Francis M. Houlihan, Editor Proceedings of SPIE Vol. 3999 (2000)

EXAMINER	DATE CONSIDERED <b>7-8-2006</b>
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EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.